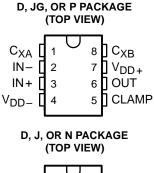
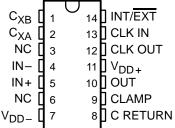
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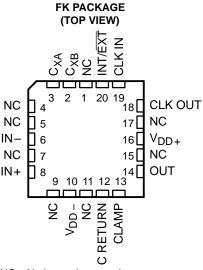
- **Input Noise Voltage**
 - 0.5 μ V (Peak-to-Peak) Typ, f = 0 to 1 Hz 1.5 μ V (Peak-to-Peak) Typ, f = 0 to 10 Hz 47 nV/ $\sqrt{\text{Hz}}$ Typ, f = 10 Hz
 - 13 nV/ $\sqrt{\text{Hz}}$ Typ, f = 1 kHz
- High Chopping Frequency . . . 10 kHz Typ
- No Clock Noise Below 10 kHz
- No Intermodulation Error Below 5 kHz
- **Low Input Offset Voltage** 10 μV Max (TLC2654A)
- **Excellent Offset Voltage Stability** With Temperature . . . 0.05 μ V/°C Max
- A_{VD} . . . 135 dB Min (TLC2654A)
- CMRR . . . 110 dB Min (TLC2654A)
- k_{SVR} . . . 110 dB Min
- Single-Supply Operation
- **Common-Mode Input Voltage Range** Includes the Negative Rail
- No Noise Degradation With External Capacitors Connected to V_{DD}_
- **Available in Q-Temp Automotive HighRel Automotive Applications** Configuration Control/Print Support Qualification to Automotive Standards

description

The TLC2654 and TLC2654A are low-noise chopper-stabilized operational amplifiers using the Advanced LinCMOS™ process. Combining this process with chopper-stabilization circuitry makes excellent dc precision possible. In addition, circuit techniques are added that give the TLC2654 and TLC2654A superior noise performance.







NC - No internal connection

Chopper-stabilization techniques provide for extremely high dc precision by continuously nulling input offset voltage even during variations in temperature, time, common-mode voltage, and power-supply voltage. The high chopping frequency of the TLC2654 and TLC2654A (see Figure 1) provides excellent noise performance in a frequency spectrum from near dc to 10 kHz. In addition, intermodulation or aliasing error is eliminated from frequencies up to 5 kHz.

This high dc precision and low noise, coupled with the extremely high input impedance of the CMOS input stage, makes the TLC2654 and TLC2654A ideal choices for a broad range of applications such as low-level. low-frequency thermocouple amplifiers and strain gauges and wide-bandwidth and subsonic circuits. For applications requiring even greater dc precision, use the TLC2652 or TLC2652A devices, which have a chopping frequency of 450 Hz.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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description (continued)

The TLC2654 and TLC2654A common-mode input voltage range includes the negative rail, thereby providing superior performance in either single-supply or split-supply applications, even at power supply voltage levels as low as ± 2.3 V.

Two external capacitors are required to operate the device; however, the on-chip chopper-control circuitry is transparent to the user. On devices in the 14-pin and 20-pin packages, the control circuitry is accessible, allowing the user the option of controlling the clock frequency with an external frequency source. In addition, the clock threshold of the TLC2554 and TLC2654A requires no level shifting when used in the single-supply configuration with a normal CMOS or TTL clock input.

Innovative circuit techniques used on the TLC2654 and TLC2654A allow exceptionally fast overload recovery time. An output clamp pin is available to reduce the recovery time even further.

The device inputs and outputs are designed to withstand -100-mA surge currents without

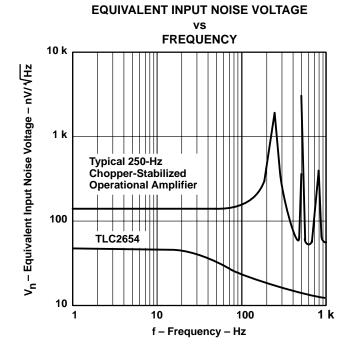


Figure 1

sustaining latch-up. In addition, the TLC2654 and TLC2654A incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015; however, exercise care in handling these devices, as exposure to ESD may result in degradation of the device parametric performance.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from -40°C to 85°C. The Q-suffix devices are characterized for operation from -40°C to 125°C. The M-suffix devices are characterized for operation over the full military temperature range of –55°C to125°C.

AVAILABLE OPTIONS

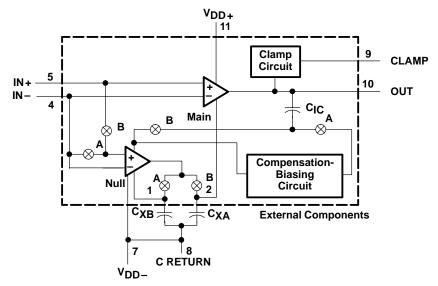
				P/	ACKAGED DEVICES	S		
_	V _{IO} max		8 PIN			14 PIN		20 PIN
TA	AT 25°C	SMALL OUTLINE (D)	CERAMIC DIP (JG)	PLASTIC DIP (P)	SMALL OUTLINE (D)	CERAMIC DIP (J)	PLASTIC DIP (N)	CERAMIC DIP (FK)
0°C to 70°C	10 μV 20 mV	TLC2654AC-8D TLC2654C-8D		TLC2654ACP TLC2654CP	TLC2654AC-14D TLC2654C-14D		TLC2654ACN TLC2654CN	_ _
-40°C to 85°C	10 μV 20 μV	TLC2654AI-8D TLC2654I-8D		TLC2654AIP TLC2654IP	TLC2654AI-14D TLC2654I-14D		TLC2654AIN TLC2654IN	_ _
-40°C to 125°C	10 μV 20 μV	TLC2654AQ-8D TLC2654Q-8D		<u> </u>	_ _	<u> </u>	<u> </u>	_ _
-55°C to 125°C	10 μV 20 μV	TLC2654AM-8D TLC2654M-8D	TLC2654AMJG TLC2654MJG	TLC2654AMP TLC2654MP	TLC2654AM-14D TLC2654M-14D	TLC2654AMJ TLC2654MJ	TLC2654AMN TLC2654MN	TLC2654AMFK TLC2654MFK

The 8-pin and 14-pin D packages are available taped and reeled. Add R suffix to device type (e.g., TLC2654AC-8DR).



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functional block diagram



Pin numbers shown are for the D (14 pin), J, and N packages.

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V _{DD+} (see Note 1)	8 V
Supply voltage, V _{DD} (see Note 1)	8 V
Differential input voltage, V _{ID} (see Note 2)	
Input voltage, V _I (any input, see Note 1)	±8 V
Voltage range on CLK IN and INT/EXT	V_{DD-} to $V_{DD-} + 5.2 V$
Input current, I _I (each input)	
Output current, IO	
Duration of short-circuit current at (or below) 25°C (see Note 3)	
Current into CLK IN and INT/EXT	
Continuous total dissipation	
Continuous total dissipation	
Operating free-air temperature range, T _A : C suffix	
Operating free-air temperature range, T _A : C suffix	0°C to 70°C
Operating free-air temperature range, T _A : C suffix	0°C to 70°C –40°C to 85°C
Operating free-air temperature range, T _A : C suffix	
Operating free-air temperature range, T _A : C suffix	
Operating free-air temperature range, T _A : C suffix I suffix Q suffix M suffix Storage temperature range	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between VDD+ and VDD-.
 - 2. Differential voltages are at IN+ with respect to IN-.
 - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D (8 pin)	725 mW	5.8 mW/°C	464 mW	377 mW	145 mW
D (14 pin)	950 mW	7.6 mW/°C	608 mW	494 mW	190 mW
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
N	1150 mW	9.2 mW/°C	736 mW	598 mW	230 mW
Р	1000 mW	8.0 mW/°C	640 mW	520 mW	200 mW

recommended operating conditions

	С	SUFFIX	18	SUFFIX	Q	SUFFIX	М	SUFFIX	UNIT	
	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNII	
Supply voltage, V _{DD±}	±2.3	±8	±2.3	±8	±2.3	±8	±2.3	±8	V	
Common-mode input voltage, V _{IC}	V_{DD-}	V _{DD+} -2.3	V							
Clock input voltage	V_{DD-}	V _{DD-} +5	V_{DD-}	V _{DD} _+5	V_{DD-}	V _{DD-} +5	V_{DD-}	V _{DD-} +5	V	
Operating free-air temperature, TA	0	70	-40	85	-40	125	-55	125	°C	



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electrical characteristics at specified free-air temperature, $V_{DD\pm}$ = ± 5 V (unless otherwise noted)

	DADAMETED	TEOT 00	NOTIONO	- +	Т	LC26540	3	TL	.C2654A	С	
	PARAMETER	I EST CO	NDITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
VIO	Input offset voltage			25°C		5	20		4	10	μV
۷IO	(see Note 4)			Full range			34			24	μν
αΛΙΟ	Temperature coefficient of input offset voltage			Full range		0.01	0.05		0.01	0.05	μV/°C
	Input offset voltage long-term drift (see Note 5)	V _{IC} = 0,	$R_S = 50 \Omega$	25°C		0.003	0.06		0.003	0.02	μV/mo
li o	Input offset current	1		25°C		30	60		30	60	pА
ΙΟ	input oilset current			Full range			150			150	PΑ
lin	Input bias current			25°C		50	60		50	60	pА
ΙΒ	input bias current			Full range			150			150	PΑ
V _{ICR}	Common-mode input voltage range	$R_S = 50 \Omega$		Full range	-5 to 2.7			-5 to 2.7			V
.,	Maximum positive peak	D 4010	One Nata O	25°C	4.7	4.8		4.7	4.8		
VOM+	output voltage swing	$R_L = 10 \text{ k}\Omega$,	See Note 6	Full range	4.7			4.7			V
\/a	Maximum negative peak	D 10 kO	Coo Noto 6	25°C	-4.7	-4.9		-4.7	-4.9		V
VOM-	output voltage swing	$R_L = 10 \text{ k}\Omega$,	See Note 6	Full range	-4.7			-4.7			V
۸. ۳-	Large-signal differential	\\o - +4\\	R _L = 10 kΩ	25°C	120	155		135	155		dB
AVD	voltage amplification	VO = ±4 V,	IN_ = 10 K22	Full range	120			130			uБ
	Internal chopping frequency			25°C		10			10		kHz
	Clamp on-state current	R _I = 100 kΩ		25°C	25			25			μА
	Ciamp on-state current	K[= 100 K22		Full range	25			25			μΑ
	Clamp off-state current	$V_{O} = -4 \text{ V to}$	0.4.1/	25°C			100			100	рA
	Ciamp on-state current	VO = -4 V to	0 4 V	Full range			100			100	PΑ
CMRR	Common-mode rejection	$V_0 = 0,$			105	125		110	125		dB
CIVINA	ratio	$V_{IC} = V_{ICR}$ min, $R_S = 50 \Omega$		Full range	105			110			uБ
kovo	Supply voltage rejection	1 1 DD = = = 2.0 1 10 = 0 1,	25°C	110	125		110	125		dB	
ksvr	ratio (ΔV _{DD±} /ΔV _{IO})		Full range	110			110			GD.	
lDD	Supply current	V _O = 0,	No load	25°C		1.5	2.4		1.5	2.4	mA
-טט	Cappi) carroin] . 0 = 0,	. 10 1000	Full range			2.5			2.5	

†Full range is 0°C to 70°C.

NOTES: 4. This parameter is not production tested full range. Thermocouple effects preclude measurement of the actual V_{IO} of these devices in high-speed automated testing. V_{IO} is measured to a limit determined by the test equipment capability at the temperature extremes. The test ensures that the stabilization circuitry is performing properly.

5. Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25° using the Arrhenius equation and assuming an activation energy of 0.96 eV.

6. Output clamp is not connected.



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operating characteristics at specified free-air temperature, $V_{DD\pm}$ = $\pm 5~V$

	PARAMETER	TEST	T. †	Τl	C26540	;	TL	C2654A	С	LINUT
	PARAMETER	CONDITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
SR+	Desitive claw rate at unity gain		25°C	1.5	2		1.5	2		\//uo
SK+	Positive slew rate at unity gain	$V_0 = \pm 2.3 \text{ V},$	Full range	1.3			1.3			V/μs
SR-	Negative slew rate at unity gain	$R_L = 10 \text{ k}\Omega$, $C_1 = 100 \text{ pF}$	25°C	2.3	3.7		2.3	3.7		V/µs
SK-	Negative siew rate at unity gain	SL = 150 pi	Full range	1.7			1.7			ν/μδ
V	Equivalent input noise voltage	f = 10 Hz	25°C		47			47	75	nV/√ Hz
Vn	(see Note 7)	f = 1 kHz	25 C		13			13	20	nv/∀HZ
V	Peak-to-peak equivalent input	f = 0 to 1 Hz	25°C		0.5			0.5		\/
VN(PP)	noise voltage	f = 0 to 10 Hz	25 0		1.5			1.5		μV
In	Equivalent input noise current	f = 10 kHz	25°C		0.004			0.004		pA/√ Hz
	Gain-bandwidth product	$f = 10 \text{ kHz},$ $R_L = 10 \text{ k}\Omega,$ $C_L = 100 \text{ pF}$	25°C		1.9			1.9		MHz
φm	Phase margin at unity gain	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	25°C		48°			48°		

[†] Full range is 0°C to 70°C.

NOTE 7: This parameter is tested on a sample basis for the TLC2654A. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.



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electrical characteristics at specified free-air temperature, V $_{DD\,\pm}$ = ±5 V (unless otherwise noted)

	DADAMETED	TECT COL	UDITIONS	- +	Т	LC2654		T	LC2654A	/I	UNIT
	PARAMETER	I ESI COI	NDITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNII
VIO	Input offset voltage			25°C		5	20		4	10	μV
VIO	(see Note 4)			Full range			40			30	μν
αΝΙΟ	Temperature coefficient of input offset voltage			Full range		0.01	0.05		0.01	0.05	μV/°C
	Input offset voltage long-term drift (see Note 5)	V _{IC} = 0,	R _S = 50 Ω	25°C		0.003	0.06		0.003	0.02	μV/mo
lio.	Input offset current			25°C		30	60		30	60	pА
ΙΟ	input onset current			Full range			200			200	pΑ
Iв	Input bias current			25°C		50	60		50	60	pА
אוי	input bias current			Full range			200			200	PΛ
VICR	Common-mode input voltage range	R _S = 50 Ω		Full range	-5 to 2.7			-5 to 2.7			V
1/	Maximum positive peak	D 4010	O - Note O	25°C	4.7	4.8		4.7	4.8		
VOM+	output voltage swing	$R_L = 10 \text{ k}\Omega$,	See Note 6	Full range	4.7			4.7			V
V	Maximum negative peak	$R_{\parallel} = 10 \text{ k}\Omega$	Soo Noto 6	25°C	-4.7	-4.9		-4.7	-4.9		V
VOM-	output voltage swing		See Note 0	Full range	-4.7			-4.7			V
AVD	Large-signal differential	V _O = ±4 V,	Pr = 10 kO	25°C	120	155		135	155		dB
^VD	voltage amplification	VO = ±4 V,	IVE = 10 K22	Full range	120			125			uБ
	Internal chopping frequency			25°C		10			10		kHz
	Clamp on-state current	R _I = 100 kΩ		25°C	25			25			μА
	Ciamp on-state current			Full range	25			25			μΑ
	Clamp off-state current	$V_0 = -4 \text{ V to}$	5.4.V	25°C			100			100	pА
	Clamp on-state current	VO = -4 V W) + V	Full range			100			100	PΛ
CMRR	Common-mode rejection	$V_0 = 0$, $V_0 = V_{10}$	nin	25°C	105	125		110	125		dB
	ratio	$R_S = 50 \Omega$	$V_{IC} = V_{ICR}$ min, $R_S = 50 \Omega$		105			110			
kevp	Supply voltage rejection	$V_{DD\pm} = \pm 2.3$		25°C	110	125		110	125		dB
ksvr	ratio (ΔV _{DD±} /ΔV _{IO})	1,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	Full range	110			110			ub	
lDD	Supply current	$V_{O} = 0$,	No load	25°C		1.5	2.4		1.5	2.4	mA
-טט		.0 = 0,	. 10 1000	Full range			2.5			2.5	

†Full range is -40°C to 85°C

NOTES: 4. This parameter is not production tested full range. Thermocouple effects preclude measurement of the actual V_{IO} of these devices in high-speed automated testing. V_{IO} is measured to a limit determined by the test equipment capability at the temperature extremes. The test ensures that the stabilization circuitry is performing properly.

6. Output clamp is not connected.



^{5.} Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

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operating characteristics at specified free-air temperature, $V_{DD\pm}$ = $\pm 5~V$

	PARAMETER	TEST	T. †	T	LC2654		TL	.C2654A	I	
	PARAMETER	CONDITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
SR+	Positive slew rate at unity gain		25°C	1.5	2		1.5	2		V/μs
SINT	Fositive siew rate at unity gain	$V_0 = \pm 2.3 \text{ V},$	Full range	1.2			1.2			ν/μ5
SR-	Negative slew rate at unity gain	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	25°C	2.3	3.7		2.3	3.7		V/μs
SK-	Negative siew rate at unity gain	OL = 100 pi	Full range	1.5			1.5			ν/μδ
V	Equivalent input noise voltage	f = 10 Hz	25°C		47			47	75	->///II-
Vn	(see Note 7)	f = 1 kHz	25 C		13			13 20		nV/√ Hz
V	Peak-to-peak equivalent input	f = 0 to 1 Hz	25°C		0.5			0.5		/
VN(PP)	noise voltage	f = 0 to 10 Hz	25°C		1.5			1.5		μV
In	Equivalent input noise current	f = 10 kHz	25°C		0.004			0.004		pA/√ Hz
	Gain-bandwidth product	$f = 10 \text{ kHz},$ $R_L = 10 \text{ k}\Omega,$ $C_L = 100 \text{ pF}$	25°C		1.9			1.9		MHz
φm	Phase margin at unity gain	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	25°C		48°			48°		

[†]Full range is -40°C to 85°C.

NOTE 7: This parameter is tested on a sample basis for the TLC2654A. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.



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electrical characteristics at specified free-air temperature, V_{DD \pm} = ± 5 V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	T _A †		LC26540 LC26541			.C2654A .C2654A		UNIT	
			'^	MIN	TYP	MAX	MIN	TYP	MAX		
\/ı0	Input offset voltage		25°C		5	20		4	10	μV	
VIO	(see Note 4)		Full range			50			40	μν	
αVIO	Temperature coefficient of input offset voltage		Full range		0.01	0.05*		0.01	0.05*	μV/°C	
	Input offset voltage long-term drift (see Note 5)	$V_{IC} = 0$, $R_S = 50 \Omega$	25°C		0.003	0.06*		0.003	0.02*	μV/mo	
lio	Input offset current		25°C		30	60		30	60	pА	
'10	input onset current]	Full range			500			500	PΑ	
I _{IB}	Input bias current		25°C		50	60		50	60	pА	
סוי	input bias carrent		Full range			500			500	P/ \	
VICR	Common-mode input voltage range	R _S = 50 Ω	Full range	-5 to 2.7			-5 to 2.7			V	
.,	Maximum positive peak	D 4010 0 N 4 0	25°C	4.7	4.8		4.7	4.8		.,	
V _{OM+}	output voltage swing	$R_L = 10 \text{ k}\Omega$, See Note 6	Full range	4.7			4.7			V	
.,	Maximum negative peak	D 40 lo Can Nata C	25°C	-4.7	-4.9		-4.7	-4.9		V	
VOM-	output voltage swing	$R_L = 10 \text{ k}\Omega$, See Note 6	Full range	-4.7			-4.7			V	
AVD	Large-signal differential	$V_{\Omega} = \pm 4 \text{ V}, R_{I} = 10 \text{ k}\Omega$	25°C	120	155		135	155		dB	
^VD	voltage amplification	VO = ±4 V, KL = 10 K22	Full range	120			120			uБ	
	Internal chopping frequency		25°C		10			10		kHz	
	Clamp on-state current	R _L = 100 kΩ	25°C	25			25			μА	
	Clamp on-state current	IVE = 100 K22	Full range	25			25			μΛ	
	Clamp off-state current	$V_0 = -4 \text{ V to } 4 \text{ V}$	25°C			100			100	pА	
	Olding on state durient	VO = 4 V 10 4 V	Full range			500			500	P/ \	
CMRR	Common-mode rejection	$V_O = 0$,	25°C	105	125		110	125		dB	
CIVIKK	ratio	$V_{IC} = V_{ICR}$ min, R _S = 50 Ω	Full range	105			110			uв	
ksvr	Supply voltage rejection	$V_{DD\pm} = \pm 2.3 \text{ V to } \pm 8 \text{ V,}$	25°C	110	125		110	125		dB	
··ovk	ratio ($\Delta V_{DD\pm}/\Delta V_{IO}$)	$V_O = 0$, $R_S = 50 \Omega$	Full range	105			110			45	
lDD	Supply current	$V_O = 0$, No load	25°C		1.5	2.4		1.5	2.4	mΑ	
יטט		- U 0, 110.0dd	Full range			2.5			2.5		

^{*} On products complaint to MIL-STD-883, Class B, this parameter is not production tested.

6. Output clamp is not connected.



[†] Full range is -40° to 125°C for Q suffix, -55° to 125°C for M suffix.

NOTES: 4. This parameter is not production tested full range. Thermocouple effects preclude measurement of the actual V_{IO} of these devices in high-speed automated testing. V_{IO} is measured to a limit determined by the test equipment capability at the temperature extremes. The test ensures that the stabilization circuitry is performing properly.

^{5.} Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

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operating characteristics at specified free-air temperature, $V_{DD\pm}$ = $\pm 5~V$

	PARAMETER	TEST CONDITIONS	T _A †	TL:	C2654Q C2654M C2654A C2654A	Q	UNIT
				MIN	TYP	MAX	
SR+	Desitive along rate at unity sain		25°C	1.5	2		1////
SK+	Positive slew rate at unity gain	Va 122V B. 40k0 C. 400 F	Full range	1.1			V/μs
SR-	No gotivo alouvrata at unity gain	$V_O = \pm 2.3 \text{ V}, R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}$	25°C	2.3	3.7		1////
SK-	Negative slew rate at unity gain		Full range	1.3			V/μs
,,	Equivalent input paige valtage	f = 10 Hz	25°C		47		->44/ 11=
V _n	Equivalent input noise voltage	f = 1 kHz	25°C		13		nV/√Hz
V	Peak-to-peak equivalent input	f = 0 to 1 Hz	25°C		0.5		\/
V _{N(PP)}	noise voltage	f = 0 to 10 Hz	25°C		1.5		μV
In	Equivalent input noise current	f = 1 kHz	25°C		0.004		pA/√ Hz
	Gain-bandwidth product	$f = 10 \text{ kHz}, R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}$	25°C		1.9		MHz
φm	Phase margin at unity gain	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	25°C		48°		

[†] Full range is -40° to 125°C for Q suffix, -55° to 125°C for M suffix.



TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V _{IO}	Input offset voltage	Distribution	2
	Normalized input offset voltage	vs Chopping frequency	3
ΙΙΟ	Input offset current	vs Chopping frequency vs Free-air temperature	4 5
I _{IB}	Input bias current	vs Common-mode input voltage vs Chopping frequency vs Free-air temperature	6 7 8
	Clamp current	vs Output voltage	9
Vом	Maximum peak output voltage swing	vs Output current vs Free-air temperature	10 11
VO(PP)	Maximum peak-to-peak output voltage swing	vs Frequency	12
CMRR	Common-mode rejection ratio	vs Frequency	13
AVD	Large-signal differential voltage amplification	vs Frequency vs Free-air temperature	14 15
	Chopping frequency	vs Supply voltage vs Free-air temperature	16 17
IDD	Supply current	vs Supply voltage vs Free-air temperature	18 19
los	Short-circuit output current	vs Supply voltage vs Free-air temperature	20 21
SR	Slew rate	vs Supply voltage vs Free-air temperature	22 23
	Voltage-follower pulse response	Small signal Large signal	24 25
V _{N(PP)}	Peak-to-peak input noise voltage	vs Chopping frequency	26, 27
٧n	Equivalent input noise voltage	vs Frequency	28
ksvr	Supply voltage rejection ratio	vs Frequency	29
	Gain-bandwidth product	vs Supply voltage vs Free-air temperature	30 31
φm	Phase margin	vs Supply voltage vs Load capacitance	32 33
	Phase shift	vs Frequency	14

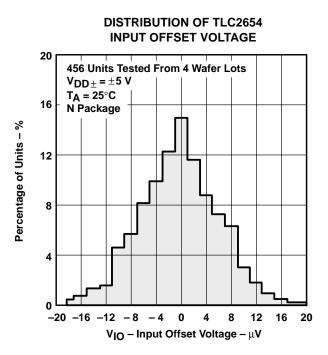
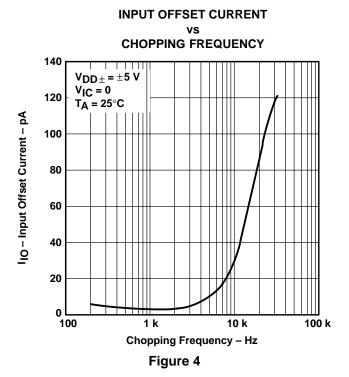


Figure 2



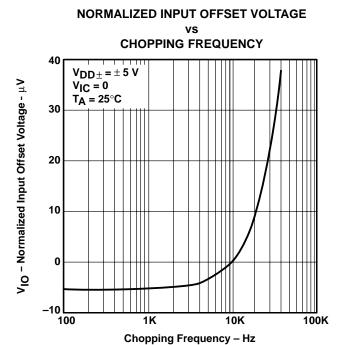
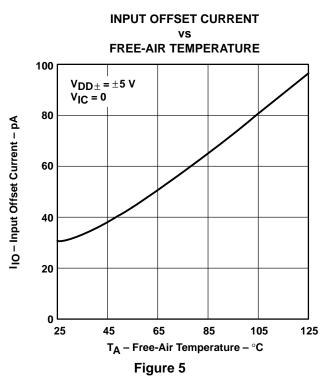
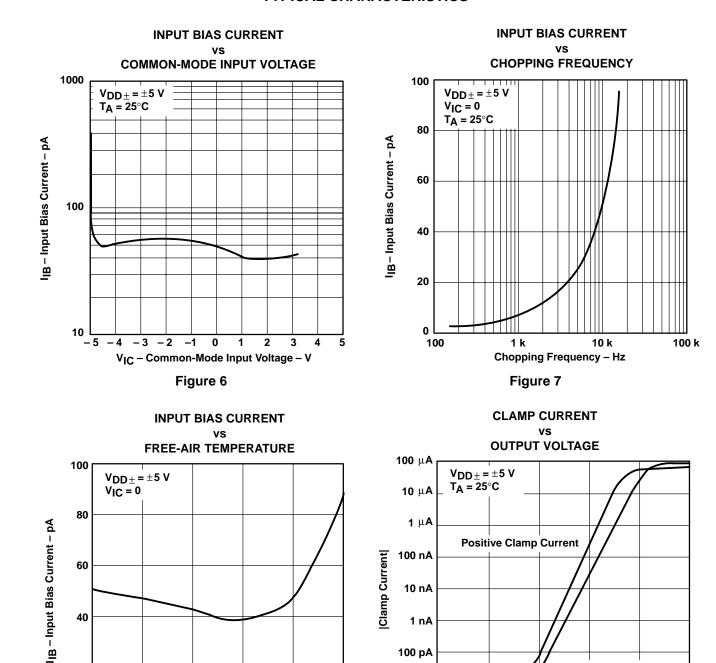


Figure 3



[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.





125

105

20

0

25

45

T_A - Free-Air Temperature - °C Figure 8



100 pA

10 pA

1 pA

4

4.2

4.4

Figure 9

|VO| - Output Voltage - V

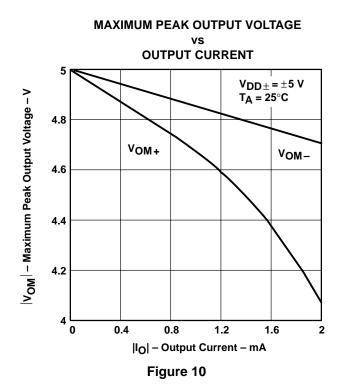
5

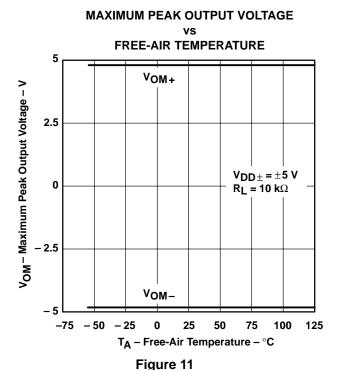
Negative Clamp Current

4.8

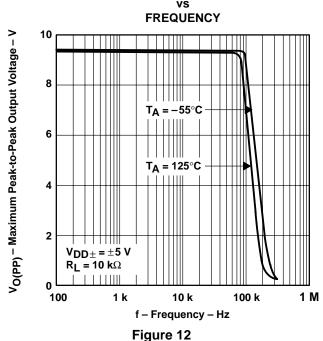
4.6

[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

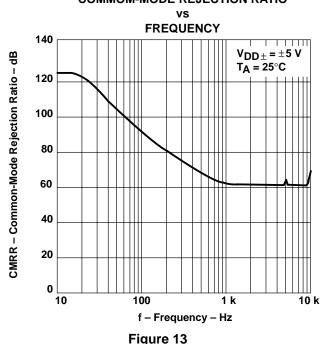




MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE



COMMOM-MODE REJECTION RATIO

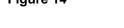


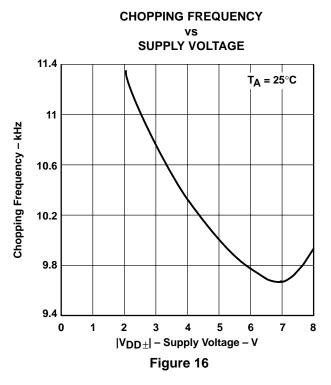
†Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



LARGE-SIGNAL DIFFERENTIAL VOLTAGE **AMPLIFICATION AND PHASE SHIFT** vs **FREQUENCY** A_{VD}' – Large-Signal Differential Voltage Amplification – dB 60° 120 100 **Phase Shift** 80° 80 100° A_{VD} 60 120° Phase Shift 40 140° 20 160° $V_{DD\pm} = \pm 5 V$ 180° $R_L = 10 \text{ k}\Omega$ $C_{I} = 100 pF$ -20 200° T_A = 25°C 220° 100 10 k 100 k 10 M 10 1 k f - Frequency - Hz Figure 14

LARGE-SIGNAL DIFFERENTIAL **VOLTAGE AMPLIFICATION** vs FREE-AIR TEMPERATURE A_{VD} - Large-Signal Differential Voltage Amplification - dB 160 $V_{DD\pm} = \pm 5 V$ $R_L = 10 \text{ k}\Omega$ V_O = ±4 V 158 156 154 152 150 75 - 50 - 25 25 50 100 75 125

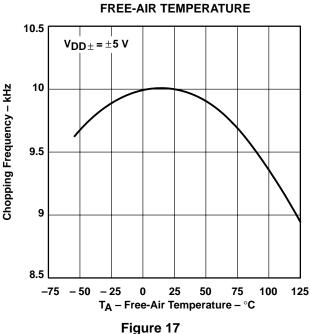




CHOPPING FREQUENCY

 T_A – Free-Air Temperature – ${}^{\circ}C$

Figure 15

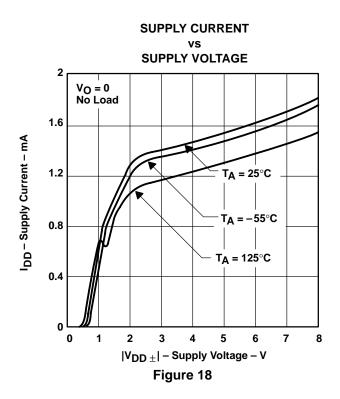


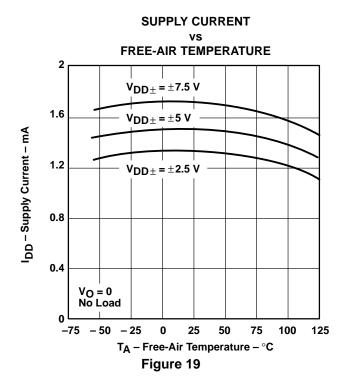
†Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

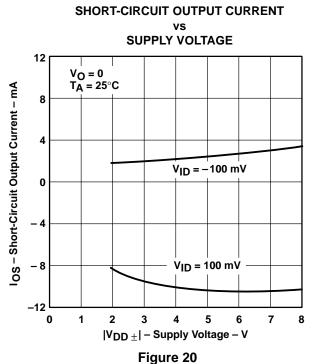


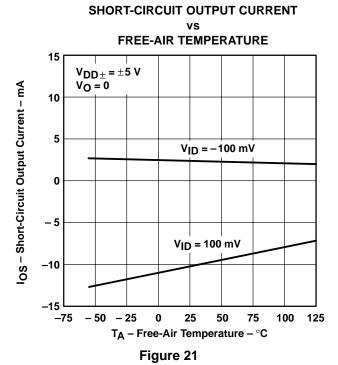
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TYPICAL CHARACTERISTICS[†]



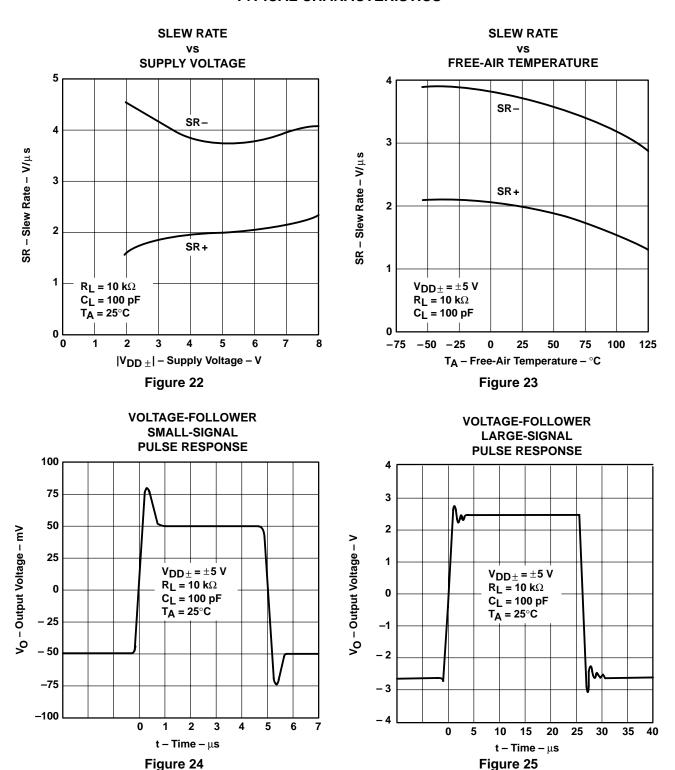






†Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



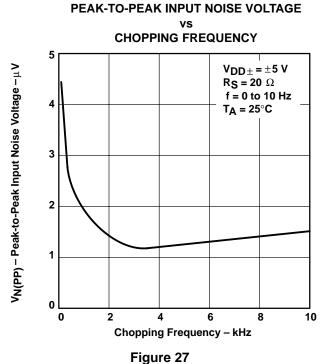


[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



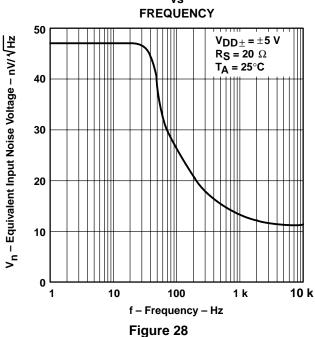
TYPICAL CHARACTERISTICS

PEAK-TO-PEAK INPUT NOISE VOLTAGE **CHOPPING FREQUENCY** 1.8 $V_{N(PP)}$ – Peak-to-Peak Input Noise Voltage – μV $V_{DD\pm} = \pm 5 V$ $R_S = 20 \Omega$ 1.6 f = 0 to 1 Hz $T_A = 25^{\circ}C$ 1.4 1.2 1 8.0 0.6 0.4 0.2 0 0 2 6 8 10 Chopping Frequency - kHz



EQUIVALENT INPUT NOISE VOLTAGE vs **FREQUENCY**

Figure 26



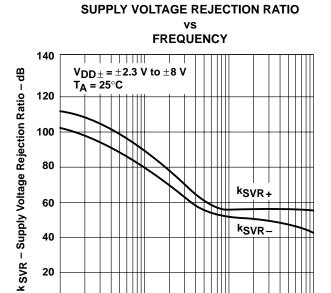


Figure 29

f - Frequency - Hz

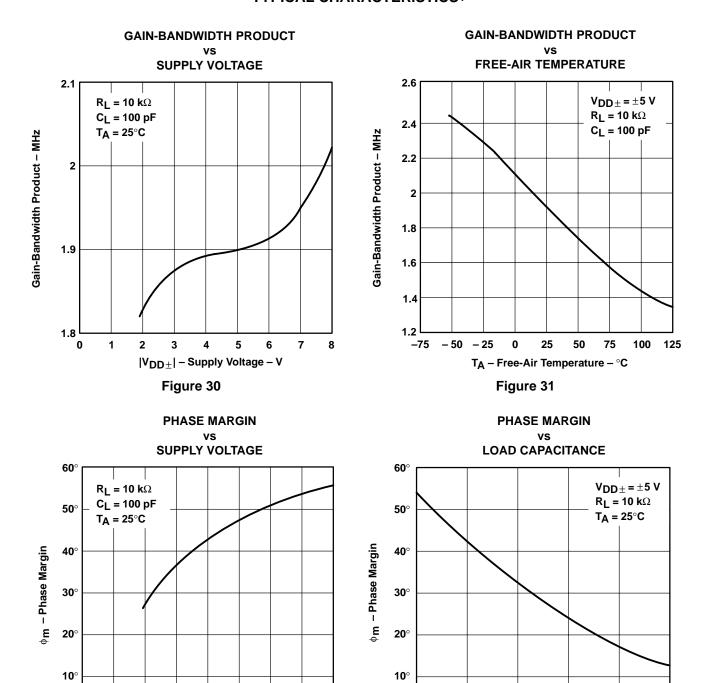
1 k

10 k

20

0

10



7

0°

0

3

4

 $|V_{DD\pm}|$ – Supply Voltage – V

Figure 32

5



0° ∟ 0

200

400

Figure 33

600

C_L - Load Capacitance - pF

800

1000

[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

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APPLICATION INFORMATION

capacitor selection and placement

Leakage and dielectric absorption are the two important factors to consider when selecting external capacitors C_{XA} and C_{XB} . Both factors can cause system degradation, negating the performance advantages realized by using the TLC2654.

Degradation from capacitor leakage becomes more apparent with increasing temperatures. Low-leakage capacitors and standoffs are recommended for operation at $T_A = 125$ °C. In addition, guard bands are recommended around the capacitor connections on both sides of the printed-circuit board to alleviate problems caused by surface leakage on circuit boards.

Capacitors with high dielectric absorption tend to take several seconds to settle upon application of power, which directly affects input offset voltage. In applications needing fast settling of input voltage, high-quality film capacitors such as mylar, polystyrene, or polypropylene should be used. In other applications, a ceramic or other low-grade capacitor can suffice.

Unlike many choppers available today, the TLC2654 is designed to function with values of C_{XA} and C_{XB} in the range of 0.1 μ F to 1 μ F without degradation to input offset voltage or input noise voltage. These capacitors should be located as close as possible to C_{XA} and C_{XB} and return to either V_{DD-} or C RETURN. On many choppers, connecting these capacitors to V_{DD-} causes degradation in noise performance; this problem is eliminated on the TLC2654.

internal/external clock

The TLC2654 has an internal clock that sets the chopping frequency to a nominal value of 10 kHz. On 8-pin packages, the chopping frequency can only be controlled by the internal clock; however, on all 14-pin packages and the 20-pin FK package the device chopping frequency can be set by the internal clock or controlled externally by use of the INT/EXT and CLK IN. To use the internal 10-kHz clock, no connection is necessary. If external clocking is desired, connect INT/EXT to V_{DD} and the external clock to CLK IN. The external clock trip point is 2.5 V above the negative rail; however, CLK IN can be driven from the negative rail to 5 V above the negative rail. This allows the TLC2654 to be driven directly by 5-V TTL and CMOS logic when operating in the single-supply configuration. If this 5-V level is exceeded, damage could occur to the device unless the current

into CLK IN is limited to ± 5 mA. A divide-by-two frequency divider interfaces with CLK IN and sets the chopping frequency. The chopping frequency appears on CLK OUT.

overload recovery/output clamp

When large differential-input-voltage conditions are applied to the TLC2654, the nulling loop attempts to prevent the output from saturating by driving C_{XA} and C_{XB} to internally-clamped voltage levels. Once the overdrive condition is removed, a period of time is required to allow the built-up charge to dissipate. This time period is defined as overload recovery time (see Figure 34). Typical overload recovery time for the TLC2654 is significantly faster than competitive products; however, this time can be reduced further by use of internal clamp circuitry accessible through CLAMP if required.

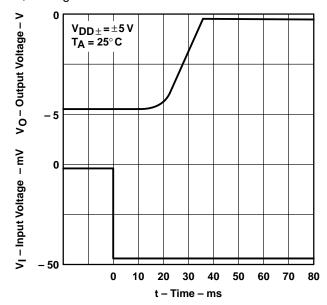


Figure 34. Overload Recovery



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APPLICATION INFORMATION

overload recovery/output clamp (continued)

The clamp is a switch that is automatically activated when the output is approximately 1 V from either supply rail. When connected to the inverting input (in parallel with the closed-loop feedback resistor), the closed-loop gain is reduced and the TLC2654 output is prevented from going into saturation. Since the output must source or sink current through the switch (see Figure 9), the maximum output voltage swing is slightly reduced.

thermoelectric effects

To take advantage of the extremely low offset voltage temperature coefficient of the TLC2654, care must be taken to compensate for the thermoelectric effects present when two dissimilar metals are brought into contact with each other (such as device leads being soldered to a printed-circuit board). It is not uncommon for dissimilar metal junctions to produce thermoelectric voltages in the range of several microvolts per degree Celsius (orders of magnitude greater than the $0.01~\mu\text{V}/^\circ\text{C}$ typical of the TLC2654).

To help minimize thermoelectric effects, pay careful attention to component selection and circuit-board layout. Avoid the use of nonsoldered connections (such as sockets, relays, switches, etc.) in the input signal path. Cancel thermoelectric effects by duplicating the number of components and junctions in each device input. The use of low-thermoelectric-coefficient components, such as wire-wound resistors, is also beneficial.

latch-up avoidance

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC2654 inputs and outputs are designed to withstand -100-mA surge currents without sustaining latch-up; however, techniques to reduce the chance of latch-up should be used whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltages should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be stunted by the use of decoupling capacitors (0.1 μ F typical) located across the supply rails as close to the device as possible.

The current path established if latch-up occurs is usually between the supply rails and is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor. The chance of latch-up occurring increases with increasing temperature and supply voltage.

electrostatic-discharge protection

The TLC2654 incorporates internal ESD-protection circuits that prevent functional failures at voltages at or below 2000 V. Care should be exercised in handling these devices, as exposure to ESD may result in degradation of the device parametric performance.

theory of operation

Chopper-stabilized operational amplifiers offer the best dc performance of any monolithic operational amplifier. This superior performance is the result of using two operational amplifiers — a main amplifier and a nulling amplifier – plus oscillator-controlled logic and two external capacitors to create a system that behaves as a single amplifier. With this approach, the TLC2654 achieves submicrovolt input offset voltage, submicrovolt noise voltage, and offset voltage variations with temperature in the nV/°C range.

The TLC2654 on-chip control logic produces two dominant clock phases: a nulling phase and an amplifying phase. The term chopper-stabilized derives from the process of switching between these two clock phases. Figure 35 shows a simplified block diagram of the TLC2654. Switches A and B are make-before-break types.

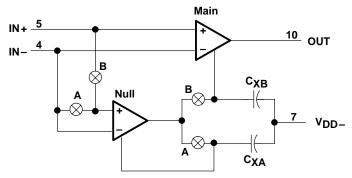


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APPLICATION INFORMATION

theory of operation (continued)

During the nulling phase, switch A is closed, shorting the nulling amplifier inputs together and allowing the nulling amplifier to reduce its own input offset voltage by feeding its output signal back to an inverting input node. Simultaneously, external capacitor C_{XA} stores the nulling potential to allow the offset voltage of the amplifier to remain nulled during the amplifying phase.



Pin numbers shown are for the D (14 pin), J, and N packages.

Figure 35. TLC2654 Simplified Block Diagram

During the amplifying phase, switch B is closed, connecting the output of the nulling amplifier to a noninverting input of the main amplifier. In this configuration, the input offset voltage of the main amplifier is nulled. Also, external capacitor C_{XB} stores the nulling potential to allow the offset voltage of the main amplifier to remain nulled during the next nulling phase.

This continuous chopping process allows offset voltage nulling during variations in time and temperature and over the common-mode input voltage range and power supply range. In addition, because the low-frequency signal path is through both the null and main amplifiers, extremely high gain is achieved.

The low-frequency noise of a chopper amplifier depends on the magnitude of the component noise prior to chopping and the capability of the circuit to reduce this noise while chopping. The use of the Advanced LinCMOS process, with its low-noise analog MOS transistors and patent-pending input stage design, significantly reduces the input noise voltage.

The primary source of nonideal operation in chopper-stabilized amplifiers is error charge from the switches. As charge imbalance accumulates on critical nodes, input offset voltage can increase especially with increasing chopping frequency. This problem has been significantly reduced in the TLC2654 by use of a patent-pending compensation circuit and the Advanced LinCMOS process.

The TLC2654 incorporates a feed-forward design that ensures continuous frequency response. Essentially, the gain magnitude of the nulling amplifier and compensation network crosses unity at the break frequency of the main amplifier. As a result, the high-frequency response of the system is the same as the frequency response of the main amplifier. This approach also ensures that the slewing characteristics remain the same during both the nulling and amplifying phases.

The primary limitation on ac performance is the chopping frequency. As the input signal frequency approaches the chopper's clock frequency, intermodulation (or aliasing) errors result from the mixing of these frequencies. To avoid these error signals, the input frequency must be less than half the clock frequency. Most choppers available today limit the internal chopping frequency to less than 500 Hz in order to eliminate errors due to the charge imbalancing phenomenon mentioned previously. However, to avoid intermodulation errors on a 500-Hz chopper, the input signal frequency must be limited to less than 250 Hz.



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APPLICATION INFORMATION

theory of operation (continued)

The TLC2654 removes this restriction on ac performance by using a 10-kHz internal clock frequency. This high chopping frequency allows amplification of input signals up to 5 kHz without errors due to intermodulation and greatly reduces low-frequency noise.

THERMAL INFORMATION

temperature coefficient of input offset voltage

Figure 36 shows the effects of package-included thermal EMF. The TLC2654 can null only the offset voltage within its nulling loop. There are metal-to-metal junctions outside the nulling loop (bonding wires, solder joints, etc.) that produce EMF. In Figure 36, a TLC2654 packaged in a 14-pin plastic package (N package) was placed in an oven at 25°C at t = 0, biased up, and allowed to stabilize. At t = 3 min, the oven was turned on and allowed to rise in temperature to 125°C. As evidenced by the curve, the overall change in input offset voltage with temperature is less than the specified maximum limit of $0.05~\mu\text{V}/^{\circ}\text{C}$.

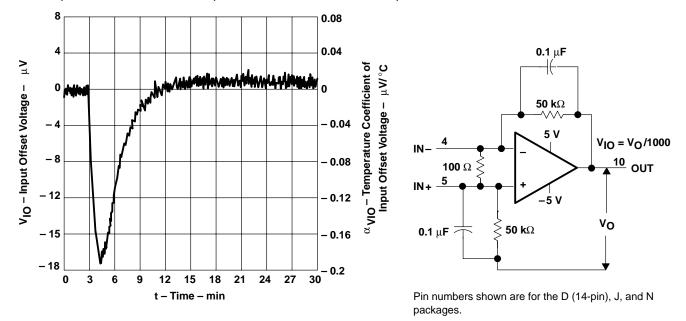


Figure 36. Effects of Package-Induced Thermal EMF





24-Aug-2018

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-9089504QPA	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	9089504QPA TLC2654AM	Sample
TLC2654AC-8D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		2654AC	Sample
TLC2654ACP	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC2654AC	Sample
TLC2654AI-8D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		2654AI	Sample
TLC2654AIP	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type		TLC2654AI	Sample
TLC2654AMJGB	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	9089504QPA TLC2654AM	Sample
TLC2654C-14DR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC2654C	Sample
TLC2654C-8D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		2654C	Sample
TLC2654C-8DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		2654C	Sample
TLC2654C-8DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		2654C	Sample
TLC2654CN	ACTIVE	PDIP	N	14	25	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC2654CN	Sample
TLC2654CP	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type		TLC2654CP	Sample
TLC2654I-8D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		26541	Sample
TLC2654I-8DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	26541	Sample
TLC2654IP	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type		TLC2654IP	Sample
TLC2654IPE4	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC2654IP	Sample

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

PACKAGE OPTION ADDENDUM



24-Aug-2018

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TLC2654A, TLC2654AM:

Catalog: TLC2654A

Military: TLC2654AM

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product





24-Aug-2018

• Military - QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device Device		Package		SPQ	Reel	Reel	A0	B0	K0	P1 .	W	Pin1
	Type	Drawing			Diameter (mm)	Width W1 (mm)	(mm)	(mm)	(mm)	(mm)	(mm)	Quadrant
TLC2654C-14DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC2654C-8DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC2654I-8DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

www.ti.com 26-Feb-2019



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
TLC2654C-14DR	SOIC	D	14	2500	350.0	350.0	43.0	
TLC2654C-8DR	SOIC	D	8	2500	340.5	338.1	20.6	
TLC2654I-8DR	SOIC	D	8	2500	340.5	338.1	20.6	

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





SMALL OUTLINE INTEGRATED CIRCUIT



- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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